

MJE13001AT (3DD13001AT)

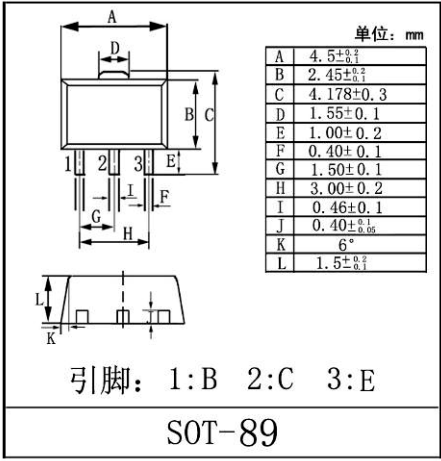
硅 NPN 半导体三极管/SILICON NPN TRANSISTOR

用途: 节能灯电路。

Purpose: High frequency electronic lighting ballast applications.

极限参数/Absolute maximum ratings(Ta=25℃)

参数符号 Symbol	数值 Rating	单位 Unit
V _{CB0}	600	V
V _{CE0}	400	V
V _{EB0}	9.0	V
I _C	0.17	A
P _c (Ta=25℃)	0.8	W
T _j	150	℃
T _{stg}	-55~150	℃



电性能参数/Electrical characteristics(Ta=25℃)

参数符号 Symbol	测试条件 Test condition	数值 Rating			单位 Unit
		最小值 Min	典型值 Typ	最大值 Max	
V _{CB0}	I _C =1mA I _E =0	600			V
V _{CE0}	I _C =10mA I _B =0	400			V
V _{EB0}	I _E =1mA I _C =0	9.0			V
I _{CB0}	V _{CB} =600V I _E =0			0.1	mA
I _{CE0}	V _{CE} =400V I _B =0			0.1	mA
I _{EB0}	V _{EB} =9.0V I _C =0			0.1	mA
h _{FE}	V _{CE} =20V I _C =20mA	10		40	
V _{CE(sat)}	I _C =50mA I _B =10mA			1	V
V _{BE(sat)}	I _C =50mA I _B =10mA			1.2	V
f _T	V _{CE} =10V I _C =50mA f=1.0MHz	5.0			MHz
t _s	V _{CE} =5V I _C =100mA (UI9600)			3	μs
t _f				1.2	μs

印章/Marking: H01A*

